

# SKM75GB12V



## SEMITRANS® 2

### SKM75GB12V

#### Features

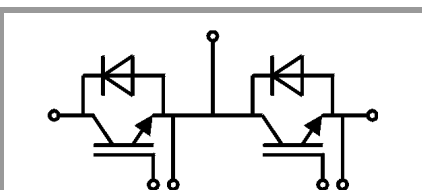
- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

#### Typical Applications\*

- AC inverter drives
- UPS
- Electronic welders

#### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$



GB

#### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	114	A
		$T_c = 80^\circ\text{C}$	87	A
$I_{Cnom}$		75	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	225	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 720\text{ V}$	$T_j = 125^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 20\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	97	A
		$T_c = 80^\circ\text{C}$	73	A
$I_{Fnom}$		75	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	225	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	430	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	200	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

#### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 75\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.85	2.30	V
		$T_j = 150^\circ\text{C}$	2.25	2.55	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.94	1.04	V
		$T_j = 150^\circ\text{C}$	0.88	0.98	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	12.13	16.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	18.27	20.93	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5.5	6	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	$\text{mA}$
		$T_j = 150^\circ\text{C}$			$\text{mA}$
$C_{ies}$	$V_{CE} = 25\text{ V}$		4.5		$\text{nF}$
$C_{oes}$	$V_{GE} = 0\text{ V}$		0.44		$\text{nF}$
$C_{res}$			0.442		$\text{nF}$
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		830		$\text{nC}$
$R_{Gint}$			10.0		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 75\text{ A}$	$T_j = 150^\circ\text{C}$	258		$\text{ns}$
$t_r$	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	32		$\text{ns}$
$E_{on}$	$R_{Gon} = 1.3\ \Omega$	$T_j = 150^\circ\text{C}$	6.7		$\text{mJ}$
$t_{d(off)}$	$R_{Goff} = 1.3\ \Omega$	$T_j = 150^\circ\text{C}$	388		$\text{ns}$
$t_f$	$di/dt_{on} = 3900\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	62		$\text{ns}$
$E_{off}$	$di/dt_{off} = 1020\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	7.1		$\text{mJ}$
	$du/dt_{off} = 9000\text{ V}/\mu\text{s}$				
$R_{th(j-c)}$	per IGBT		0.38		$\text{K/W}$

# SKM75GB12V



SEMITRANS® 2

## SKM75GB12V

### Features

- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

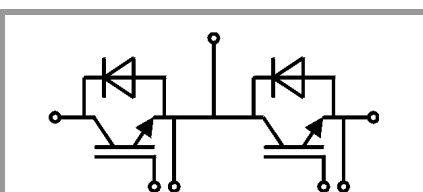
### Typical Applications\*

- AC inverter drives
- UPS
- Electronic welders

### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  
 $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 75\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.17	2.49	V
		$T_j = 150^\circ\text{C}$		2.11	2.42	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		11.6	13.2	m $\Omega$
		$T_j = 150^\circ\text{C}$		16.1	17.6	m $\Omega$
$I_{RRM}$	$I_F = 75\text{ A}$	$T_j = 150^\circ\text{C}$		85		A
$Q_{rr}$	$di/dt_{off} = 2950\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		10		$\mu\text{C}$
$E_{rr}$	$V_{GE} = \pm 15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		4.2		mJ
$R_{th(j-c)}$	per diode				0.58	K/W
<b>Module</b>						
$L_{CE}$					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.65		m $\Omega$
		$T_c = 125^\circ\text{C}$		1		m $\Omega$
$R_{th(c-s)}$	per module			0.04	0.05	K/W
$M_s$	to heat sink M6		3		5	Nm
$M_t$		to terminals M5	2.5		5	Nm
						Nm
$w$					160	g



GB

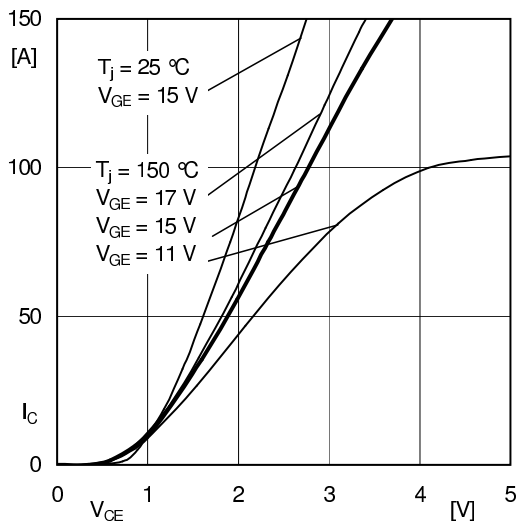


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE}$

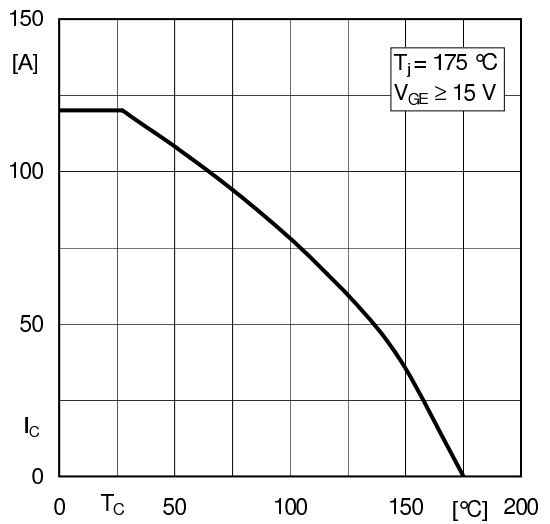


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

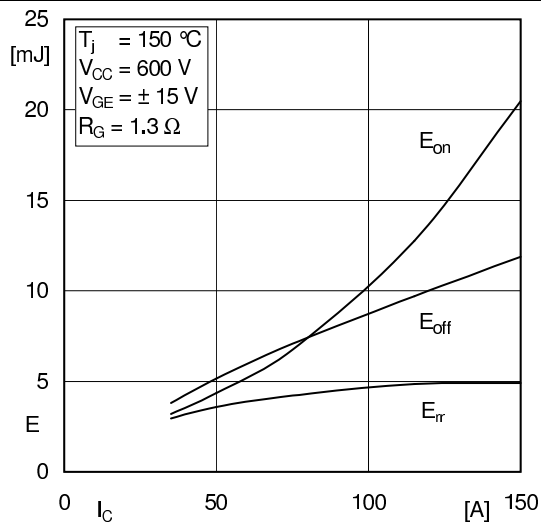


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

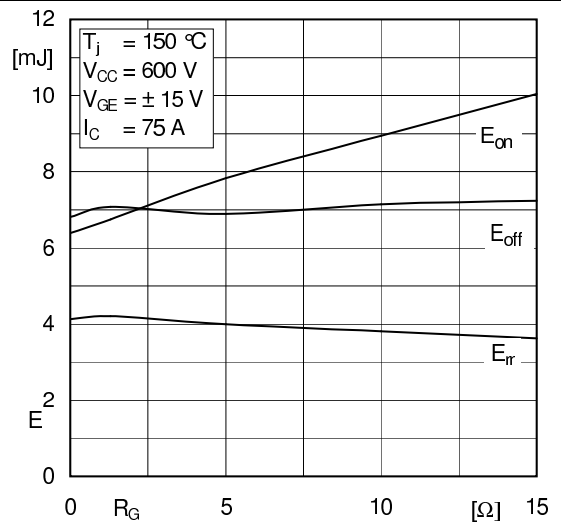


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

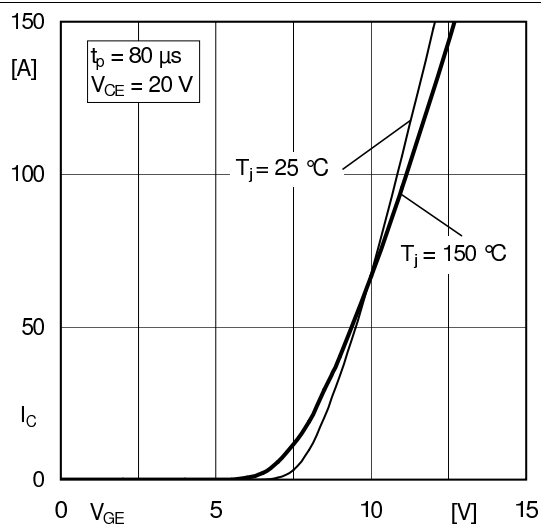


Fig. 5: Typ. transfer characteristic

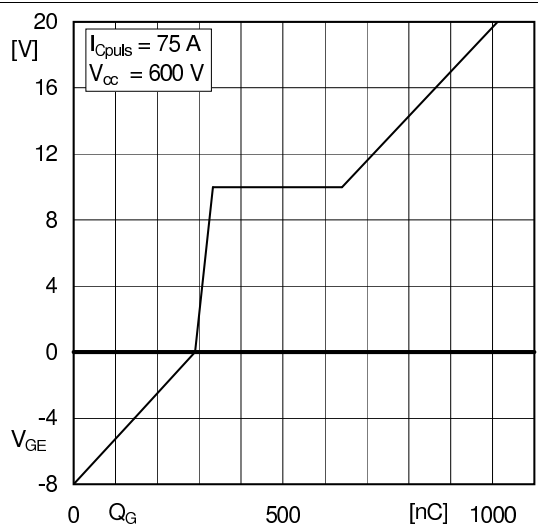


Fig. 6: Typ. gate charge characteristic

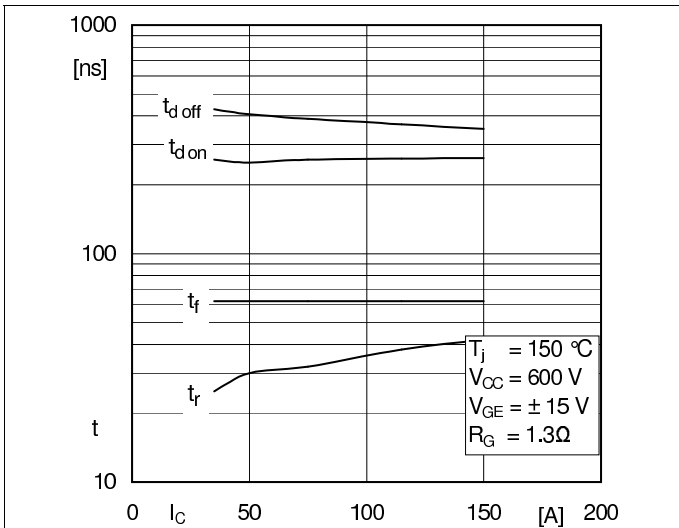


Fig. 7: Typ. switching times vs.  $I_C$

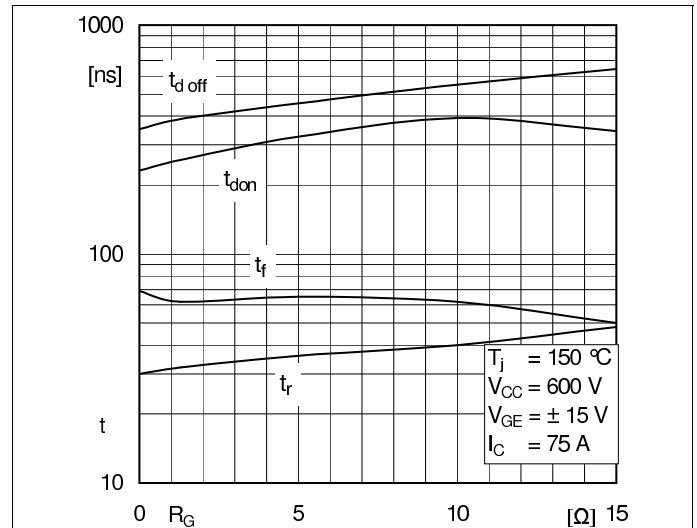


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

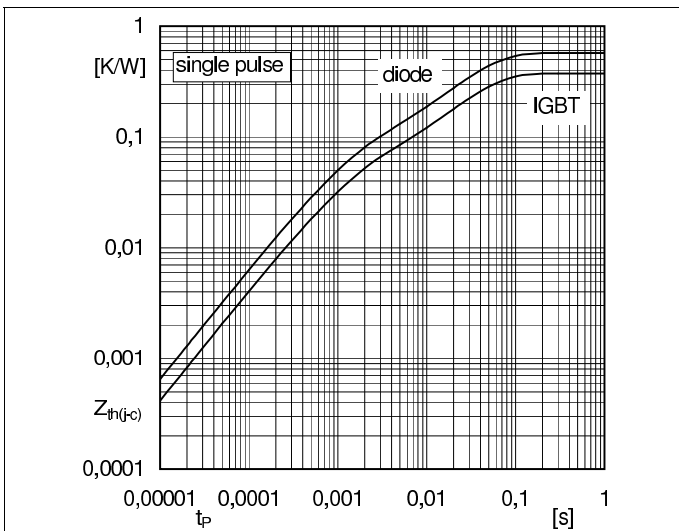


Fig. 9: Transient thermal impedance

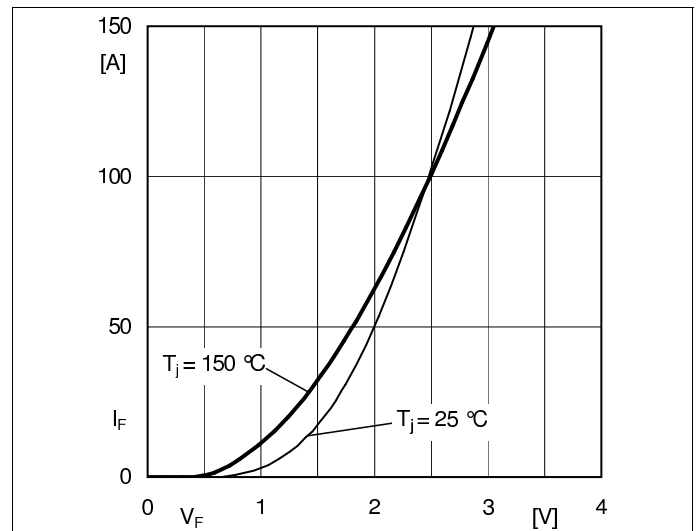


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC+EE}$

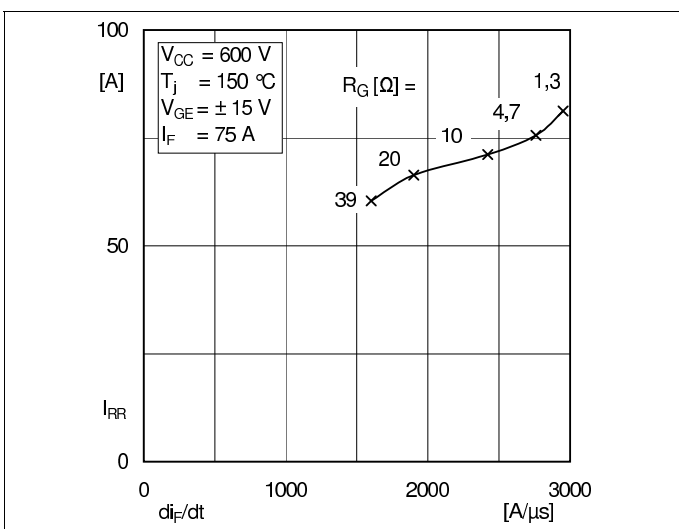


Fig. 11: CAL diode peak reverse recovery current

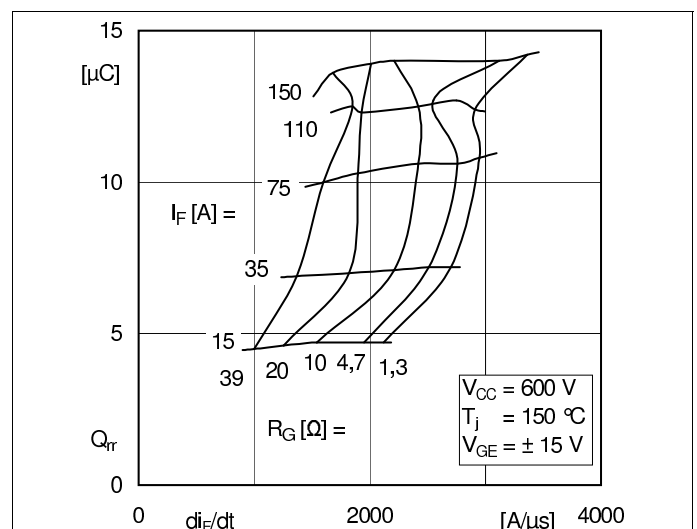


Fig. 12: Typ. CAL diode peak reverse recovery charge

